



DNLS320A

LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complimentary PNP Type Available (DPLS320A)
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings	$@T_A = 25^{\circ}C$ unless otherwise specified
-----------------	-------------------------------------------------

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	20	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	5	V
Peak Pulse Current	I _{CM}	5	А
Repetitive Peak Pulse Current (Note 3)	I _{CRP}	3	А
Continuous Collector Current	Ic	2	А
Base Current	Ι _Β	0.5	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ T _A = 25°C	PD	600	mW
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	R _{0JA}	209	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

3. Operated under pulse conditions: Pulse width \leq 100ms, duty cycle \leq 0.25.

4. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 5)				•		•
Collector Base Cutoff Current	1	_	_	100	nA	$V_{CB} = 20V, I_E = 0$
Collector-Base Cutoff Current	I _{CBO}	_	_	50	μΑ	V _{CB} = 20V, I _E = 0, T _A = 150°C
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5V, I_{C} = 0$
Collector-Base Breakdown Voltage	V _{(BR)CBO}	20	_		V	I _C = 100μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	20	_		V	I _C = 10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	_		V	I _E = 100μA
ON CHARACTERISTICS (Note 5)						
		220	—			$V_{CE} = 2V, I_{C} = 0.1A$
		220				$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	h _{FE}	220	—		—	$V_{CE} = 2V, I_C = 1A$
		200		—		$V_{CE} = 2V, I_C = 2A$
		150	_			$V_{CE} = 2V, I_C = 3A$
		_	_	70		$I_{C} = 0.5A, I_{B} = 50mA$
		_	_	120		$I_{C} = 1A, I_{B} = 50mA$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	230	mV	$I_{C} = 2A, I_{B} = 40mA$
		_	_	210		$I_{\rm C} = 2A, I_{\rm B} = 200 {\rm mA}$
		_	_	310		I _C = 3A, I _B = 300mA
Equivalent On-Resistance	R _{CE(SAT)}	_	85	105	mΩ	$I_E = 2A, I_B = 200mA$
Base-Emitter Saturation Voltage		_	_	1.1	V	$I_{C} = 2A, I_{B} = 40mA$
Dase-Emilier Saturation voltage	VBE(SAT)	_	_	1.2	V	I _C = 3A, I _B = 300mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}			1.2	V	$V_{CE} = 2V, I_C = 1A$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤	100	220	—	MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz
Output Capacitance	C _{ob}	_		35	pF	$V_{CB} = 10V, f = 1MHz$

Notes: 5. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.













Ordering Information (Note 6)

Device	Packaging	Shipping
DNLS320A-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



N3A = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key												
Year	2008		2009	2010		2011	2012	2	2013	2014	•	2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.